



IN THE SPECIFICATION

Please amend the written specification as follows:

Please replace the paragraph starting on page 3, line 20 to page 4, line 7 in the original specification with the following amended paragraph:

A fourth prior art process is described by L.W. Cheng et al., *Thin Solid Films*, 355-356, 412 (1999). In this process, a single crystal silicon substrate is implanted with nitrogen ions prior to doping the source/drain junction. Additional procedures including doping the source/drain junction, depositing nickel onto silicon, and annealing the sample are then performed. Nitrogen ion implantation is found to slow down dopant diffusion and delay transformation from nickel mono-silicide to nickel-disilicide during the high temperature annealing. The process controls dopant transport in shallow source/drain junctions in silicon, but does not improve silicidation of nickel on poly-silicon device structures such as gates. Furthermore, source/drain dopants (particularly Boron) were poorly activated.

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